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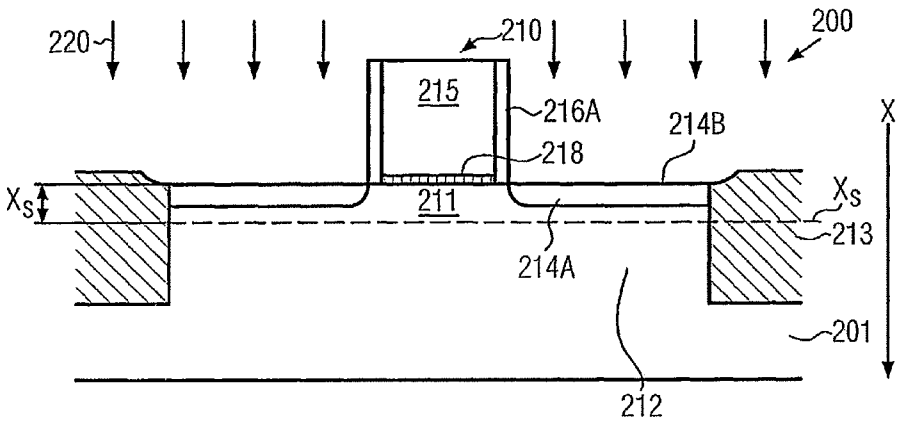
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(54) **Title:** TECHNIQUE FOR REDUCING SILICIDE NON-UNIFORMITIES BY ADAPTING AVERTICAL DOPANT PROFILE



(57) **Abstract:** By modifying the vertical dopant concentration in deep drain and source regions, the reaction behavior during the formation of metal suicide regions 217 may be controlled. For this purpose, an increased dopant concentration is formed around a target depth (X_s) for the metal suicide interface, thereby reducing the reaction speeds and thus improving the uniformity of the resulting metal suicide interface.

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